

HSB278S

Silicon Schottky Barrier Diode for High Speed Switching

HITACHI

ADE-208-1383 (Z)
Rev.0
Mar. 2001

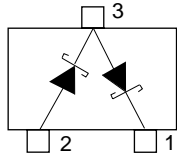
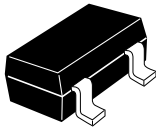
Features

- Low forward voltage, Low capacitance.
- CMPAK package is suitable for high density surface mounting and high speed assembly.

Ordering Information

Type No.	Laser Mark	Package Code
HSB278S	S2	CMPAK

Outline



(Top View)

- 1 Cathode 2
- 2 Anode 1
- 3 Cathode 1
Anode 2

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Item	Symbol	Value	Unit
Repetitive peak reverse voltage	V_{RRM}	30	V
Reverse voltage	V_R	30	V
Non-Repetitive peak forward surge current	$I_{FSM}^{*1 *2}$	200	mA
Peak forward current	I_{FM}^{*2}	150	mA
Average rectified current	I_O^{*2}	30	mA
Junction temperature	T_j	125	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +125	$^\circ\text{C}$

- Notes: 1. 10 msec sine wave 1 pulse
 2. Per one device.

Electrical Characteristics ($T_a = 25^\circ\text{C}$) *¹

Item	Symbol	Min	Typ	Max	Unit	Test Condition
Forward voltage	V_{F1}	—	—	0.30	V	$I_F = 1 \text{ mA}$
	V_{F2}	—	—	0.95		$I_F = 30 \text{ mA}$
Reverse current	I_R	—	—	700	nA	$V_R = 10 \text{ V}$
Capacitance	C	—	—	1.50	pF	$V_R = 1 \text{ V}$, $f = 1 \text{ MHz}$
ESD-Capability * ¹	—	100	—	—	V	$C = 200 \text{ pF}$, $R_L = 0 \Omega$, Both forward and reverse direction 1 pulse.

- Notes: 1. Per one device.
 2. Failure criterion ; $I_R > 1.4 \mu\text{A}$ at $V_R = 10 \text{ V}$

Main Characteristic

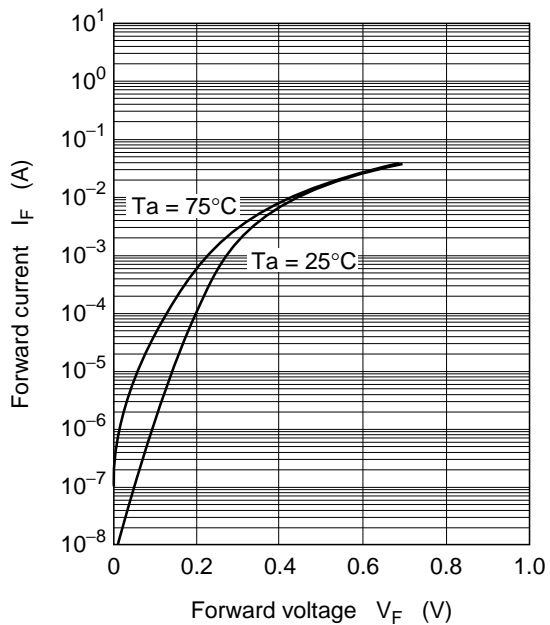


Fig.1 Forward current Vs. Forward voltage

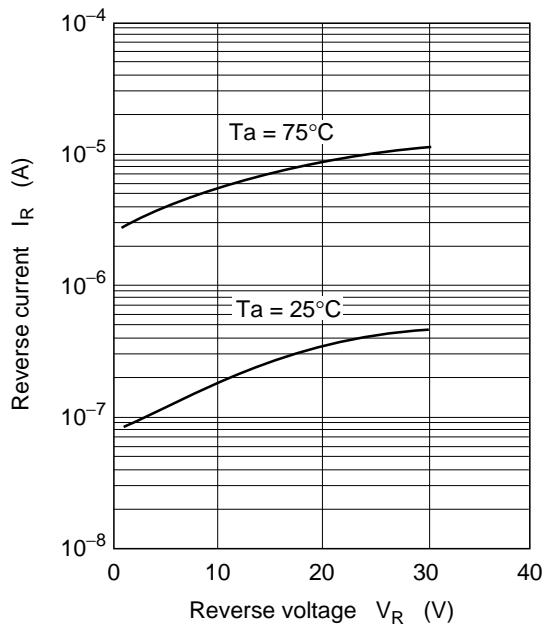


Fig.2 Reverse current Vs. Reverse voltage

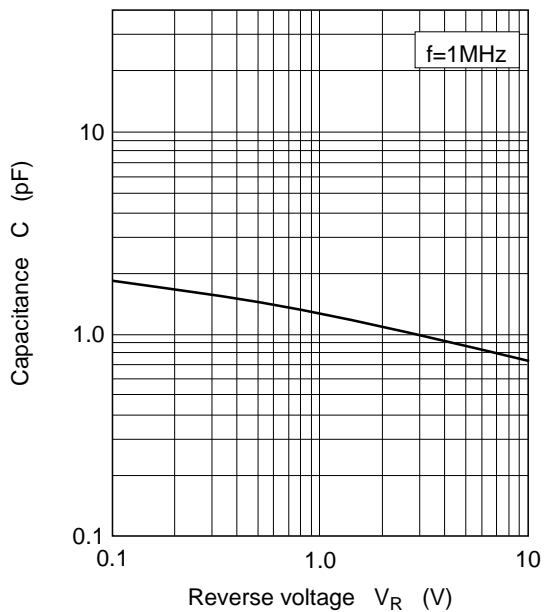
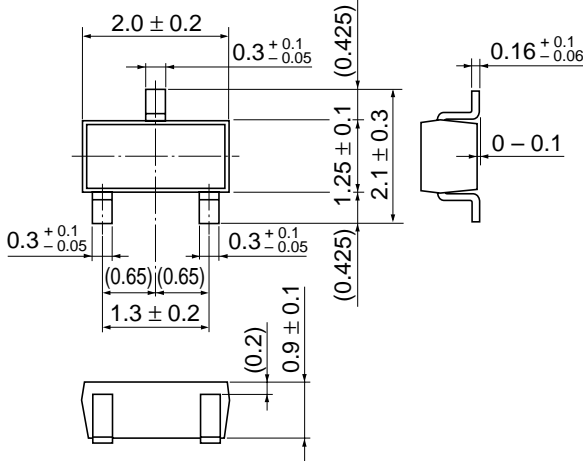


Fig.3 Capacitance Vs. Reverse voltage

Package Dimensions

As of January, 2001
Unit: mm



Hitachi Code	CMPAK
JEDEC	—
EIAJ	Conforms
Mass (reference value)	0.006 g

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